

FX6KMJ-2

High-Speed Switching Use
Pch Power MOS FET

REJ03G0262-0100

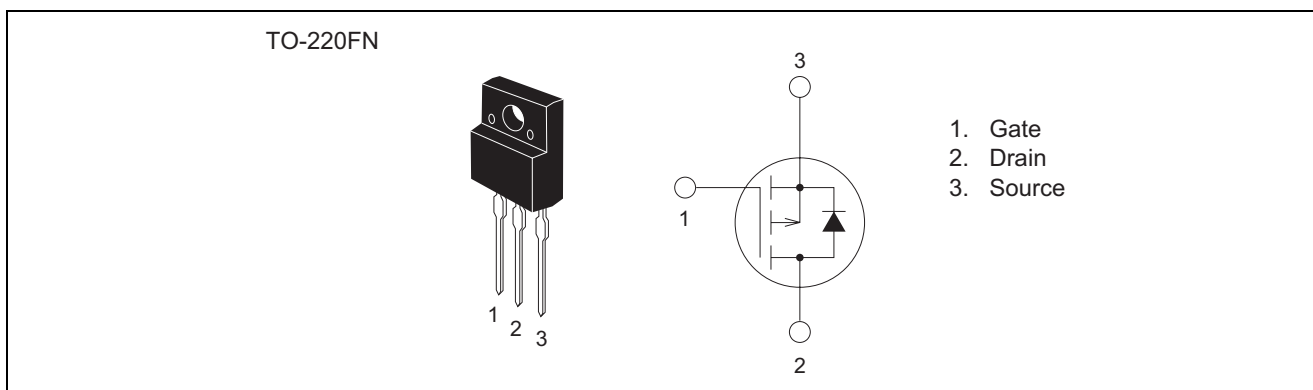
Rev.1.00

Aug.20.2004

Features

- Drive voltage : 4 V
- $V_{DSS} : -100 \text{ V}$
- $r_{DS(ON) (max)} : 0.58 \Omega$
- $I_D : -6 \text{ A}$
- Recovery Time of the Integrated Fast Recovery Diode (TYP.) : 80 ns

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

($T_c = 25^\circ\text{C}$)

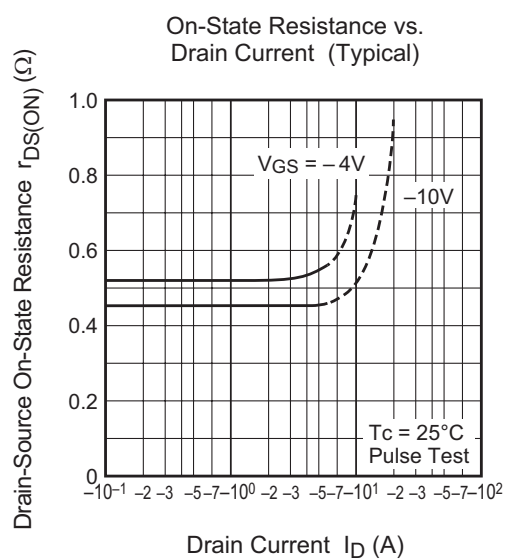
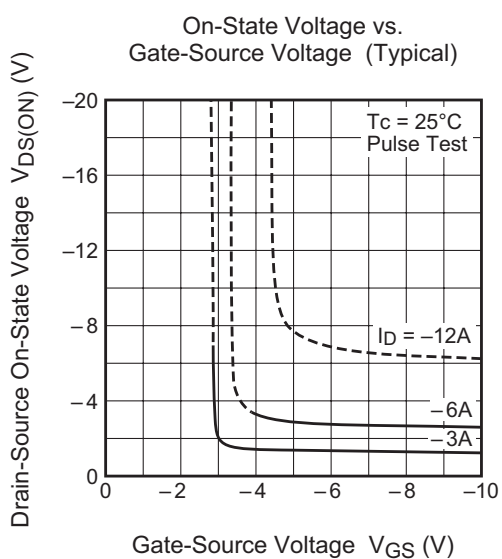
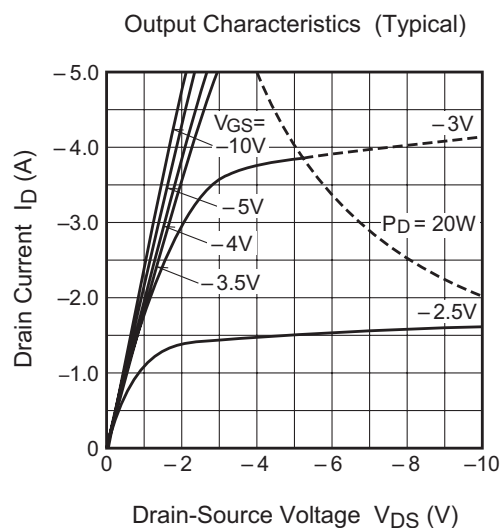
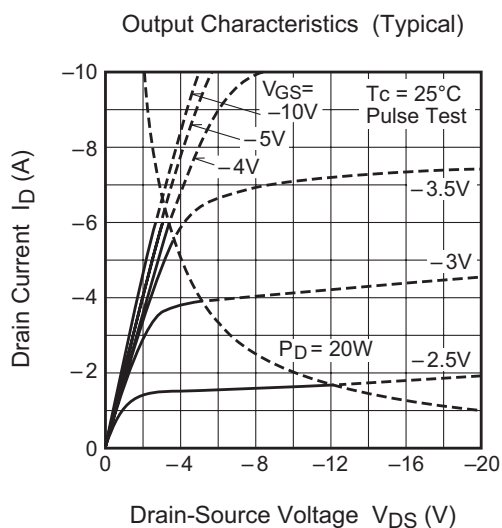
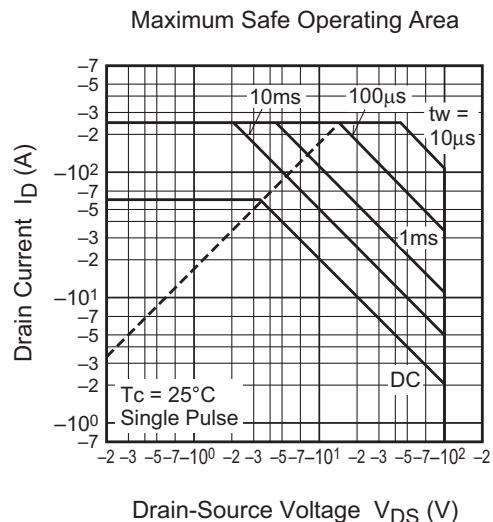
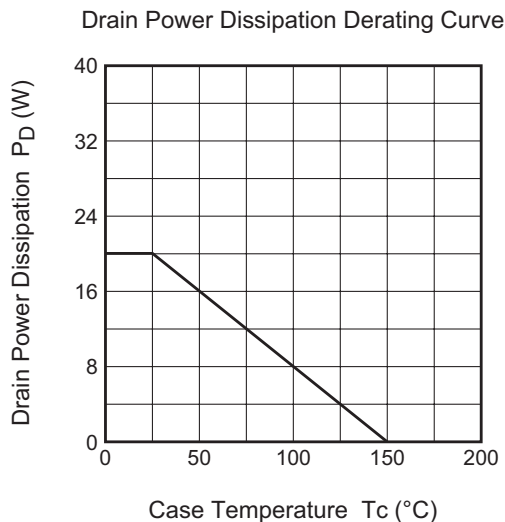
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	-100	V	$V_{GS} = 0 \text{ V}$
Gate-source voltage	V_{GSS}	± 20	V	$V_{DS} = 0 \text{ V}$
Drain current	I_D	-6	A	
Drain current (Pulsed)	I_{DM}	-24	A	
Avalanche current (Pulsed)	I_{DA}	-6	A	$L = 100 \mu\text{H}$
Source current	I_S	-6	A	
Source current (Pulsed)	I_{SM}	-24	A	
Maximum power dissipation	P_D	20	W	
Channel temperature	T_{ch}	-55 to +150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	
Isolation voltage	V_{iso}	2000	V	AC 1 minute, Terminal to case
Mass	—	2.0	g	Typical value

Electrical Characteristics

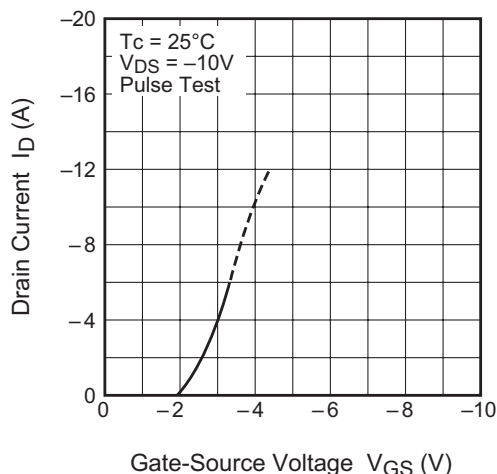
(Tch = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	-100	—	—	V	$I_D = -1 \text{ mA}$, $V_{GS} = 0 \text{ V}$
Gate-source leakage current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$
Drain-source leakage current	I_{DSS}	—	—	-0.1	mA	$V_{DS} = -100 \text{ V}$, $V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	-1.0	-1.5	-2.0	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Drain-source on-state resistance	$r_{DS(on)}$	—	0.46	0.58	Ω	$I_D = -3 \text{ A}$, $V_{GS} = -10 \text{ V}$
Drain-source on-state resistance	$r_{DS(on)}$	—	0.55	0.72	Ω	$I_D = -3 \text{ A}$, $V_{GS} = -4 \text{ V}$
Drain-source on-state voltage	$V_{DS(on)}$	—	-1.38	-1.74	V	$I_D = -3 \text{ A}$, $V_{GS} = -10 \text{ V}$
Forward transfer admittance	$ y_{fs} $	—	4.7	—	S	$I_D = -3 \text{ A}$, $V_{DS} = -5 \text{ V}$
Input capacitance	C_{iss}	—	1110	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	108	—	pF	
Reverse transfer capacitance	C_{rss}	—	44	—	pF	
Turn-on delay time	$t_{d(on)}$	—	9	—	ns	$V_{DD} = -50 \text{ V}$, $I_D = -3 \text{ A}$, $V_{GS} = -10 \text{ V}$, $R_{GEN} = R_{GS} = 50 \Omega$
Rise time	t_r	—	8	—	ns	
Turn-off delay time	$t_{d(off)}$	—	72	—	ns	
Fall time	t_f	—	33	—	ns	
Source-drain voltage	V_{SD}	—	-1.0	-1.5	V	$I_S = -3 \text{ A}$, $V_{GS} = 0 \text{ V}$
Thermal resistance	$R_{th(ch-c)}$	—	—	6.25	$^{\circ}\text{C/W}$	Channel to case
Reverse recovery time	t_{rr}	—	80	—	ns	$I_S = -6 \text{ A}$, $dis/dt = 100 \text{ A}/\mu\text{s}$

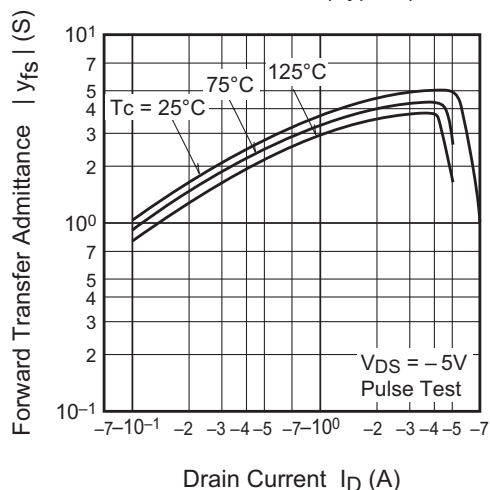
Performance Curves



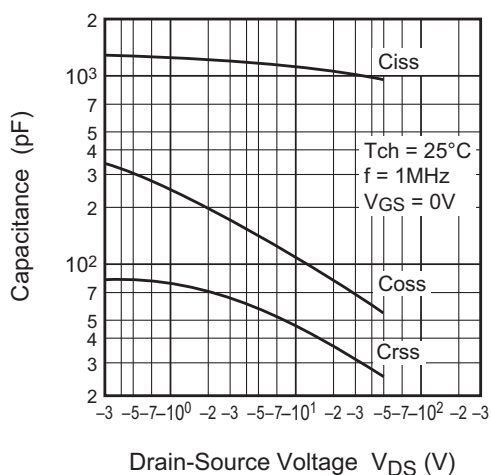
Transfer Characteristics (Typical)



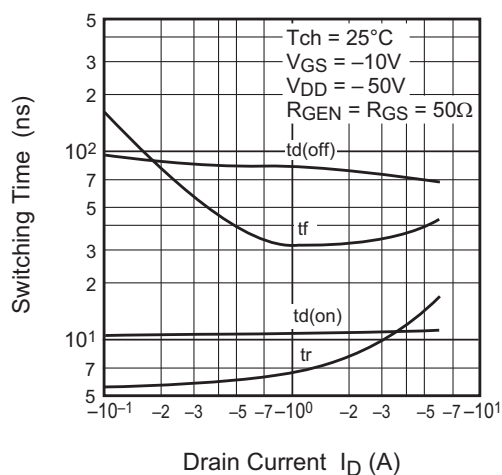
Forward Transfer Admittance vs. Drain Current (Typical)



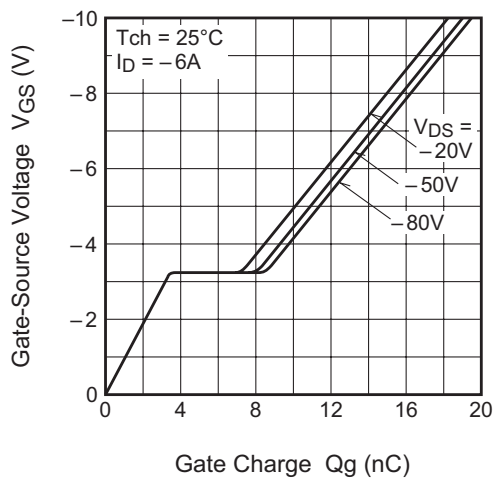
Capacitance vs. Drain-Source Voltage (Typical)



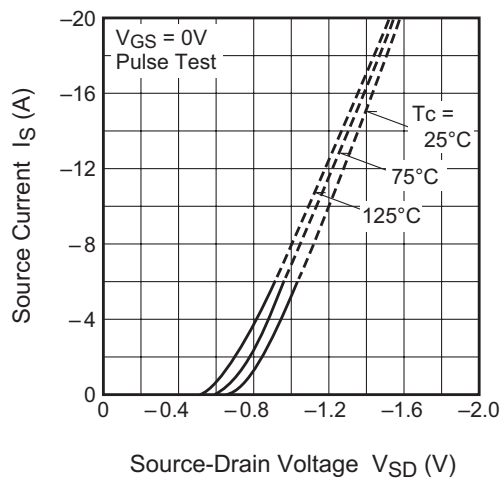
Switching Characteristics (Typical)

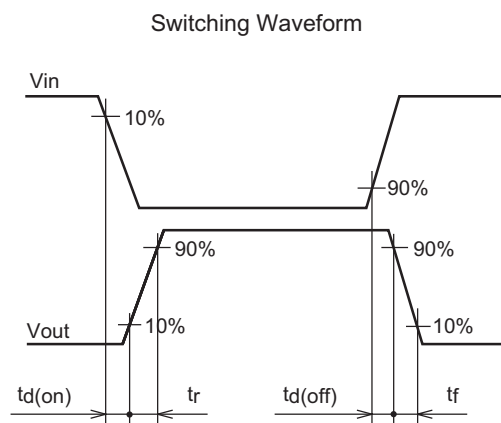
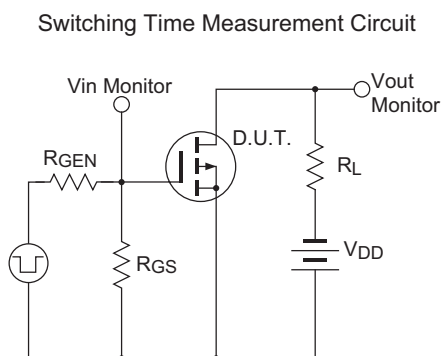
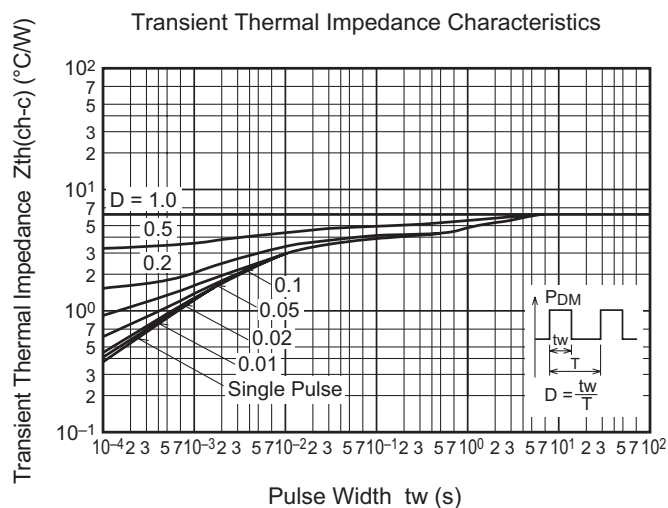
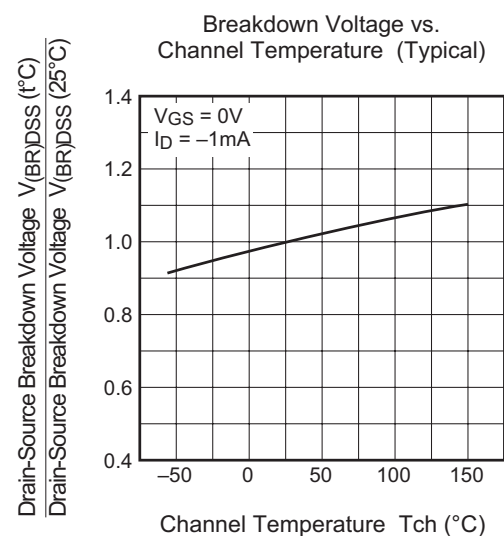
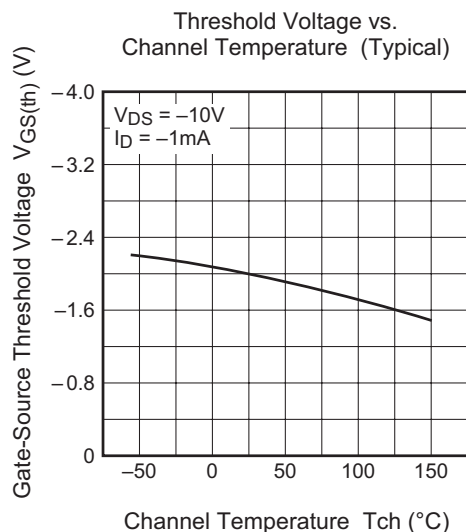
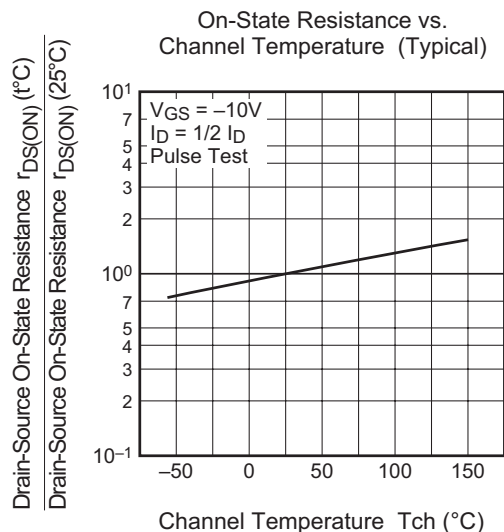


Gate-Source Voltage vs. Gate Charge (Typical)



Source-Drain Diode Forward Characteristics (Typical)

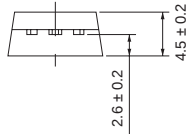
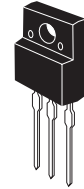
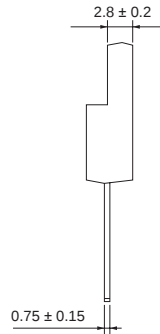
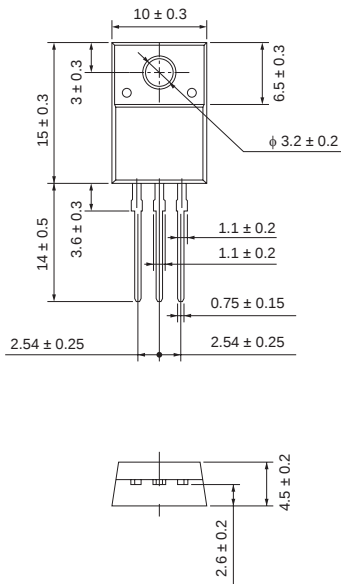




Package Dimensions

TO-220FN

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy



Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	FX6KMJ-2
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	FX6KMJ-2-A8

Note : Please confirm the specification about the shipping in detail.

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